2SK3044

Silicon N-channel power MOSFET

■ Features

- Avalanche energy capability guaranteed: EAS > 130 mJ
- \bullet Gate-source surrender voltageV_{GSS}: ± 30 V guaranteed
- High-speed switching
- No secondary breakdown

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V _{DSS}	450	V	
Gate-source surrender voltage	V _{GSS}	±30	V	
Drain current	I_{D}	±7	A	
Peak drain current	I_{DP}	±14	A	
Avalanche energy capability *	EAS	130	mJ	
Power dissipation	$P_{\rm D}$	40	W	
$T_a = 25^{\circ}C$		2		
Channel temperature	T _{ch}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	

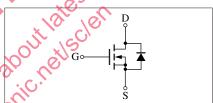
Note) *: L = 5.4 mH, $I_L = 7 \text{ A}$, 1 pulse

■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

9.9±0.3	Unit: mm
3.0+0.5	2.9±0.2
ψ3.2 φ3.2	<u>2±0.1</u>
15.	
1.4±0.2 1.6±0.2	2.6±0.1
2 0 1.6±0.1	0.55±0.15
S S S S S S S S S S S S S S S S S S S	
2.54±0.30 5.08±0.50	
1 2 3	2: Gate 2: Drain 3: Source
	TO-220D-A1 Package

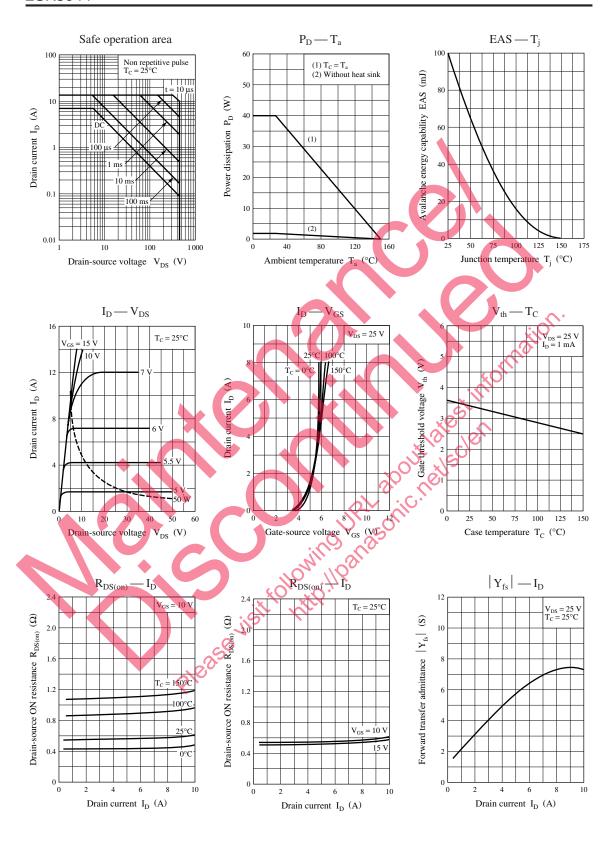
Marking Symbol: K3044

Internal Connection

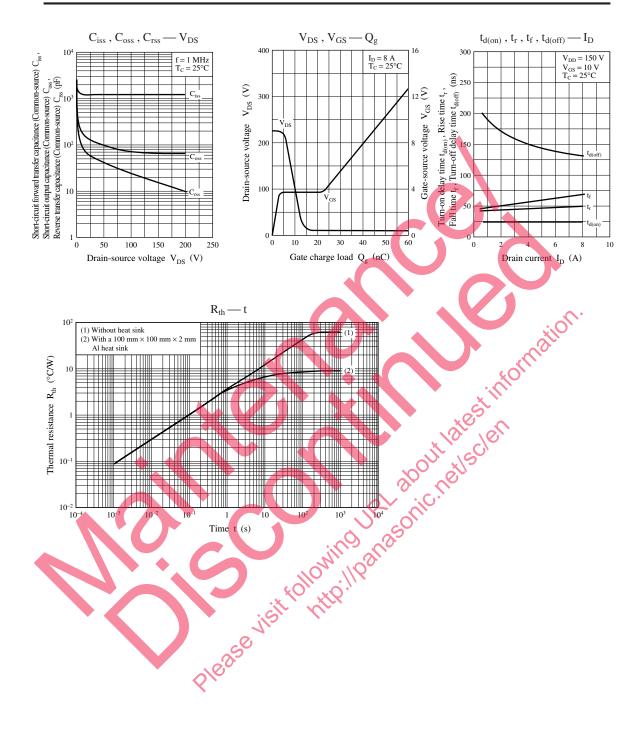


Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V _{DSS}	$I_{\rm D} = 1 \text{ mA}, V_{\rm GS} = 0$	450			V
Drain-source cutoff current	I _{DSS}	$V_{DS} = 360 \text{ V}, V_{CS} = 0$			100	μΑ
Gate-source cutoff current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$			±1	μΑ
Gate threshold voltage	V _{th}	$V_{DS} = 25 \text{ V}, I_D = 1 \text{ mA}$	2.0		5.0	V
Forward transfer admittance	Yfs	$V_{DS} = 25 \text{ V}, I_D = 4 \text{ A}$	3.0	5.0		S
Drain-source ON resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$		0.56	0.75	Ω
Diode forward voltage	OF	$I_{DR} = 7 \text{ A}, V_{GS} = 0$			-1.7	V
Short-circuit forward transfer capacitance (Common source)	C _{iss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		1300		pF
Short-circuit output capacitance (Common source)	C _{oss}			160		pF
Reverse transfer capacitance (Common source)	C _{rss}			70		pF
Turn-on delay time	t _{d(on)}	$V_{DD} = 150 \text{ V}, I_D = 4 \text{ A}, R_L = 37.5 \Omega$		25		ns
Rise time	t _r	$V_{GS} = 10 \text{ V}$		45		ns
Fall time	$t_{\rm f}$			50		ns
Turn-off delay time	t _{d(off)}			150		ns
Thermal resistance (ch-c)	R _{th(ch-c)}				3.1	°C/W
Thermal resistance (ch-a)	R _{th(ch-a)}				62.5	°C/W

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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